Title (en)

CIRCUITS WITH LINEAR FINFET STRUCTURES

Title (de)

SCHALTUNGEN MIT LINEAREN FINFET-STRUKTUREN

Title (fr)

CIRCUITS AVEC STRUCTURES DE FINFET LINÉAIRES

Publication

EP 2803077 A4 20151104 (EN)

Application

EP 13735704 A 20130113

Priority

- US 201261586387 P 20120113
- US 201261589224 P 20120120
- US 2013021345 W 20130113

Abstract (en)

[origin: WO2013106799A1] A first transistor has source and drain regions within a first diffusion fin. The first diffusion fin projects from a surface of a substrate. The first diffusion fin extends lengthwise in a first direction from a first end to a second end of the first diffusion fin. A second transistor has source and drain regions within a second diffusion fin. The second diffusion fin projects from the surface of the substrate. The second diffusion fin extends lengthwise in the first direction from a first end to a second end of the second diffusion fin. The second diffusion fin is positioned next to and spaced apart from the first diffusion fin. Either the first end or the second end of the second diffusion fin is positioned in the first direction between the first end and the second end of the first diffusion fin.

IPC 8 full level

H01L 21/8238 (2006.01); **H01L 21/28** (2006.01); **H01L 27/092** (2006.01); **H01L 27/118** (2006.01); H01L 27/02 (2006.01); H01L 29/66 (2006.01)

CPC (source: CN EP KR)

H01L 21/28123 (2013.01 - CN EP); **H01L 21/823821** (2013.01 - CN EP); **H01L 27/0207** (2013.01 - CN EP); **H01L 27/0924** (2013.01 - CN EP); **H01L 27/105** (2013.01 - CN); **H01L 27/11807** (2013.01 - CN EP); **H01L 29/41725** (2013.01 - CN); **H01L 29/6681** (2013.01 - CN EP); **H01L 29/7809** (2013.01 - KR); **H01L 29/785** (2013.01 - KR)

Citation (search report)

- [XY] US 2008308880 A1 20081218 - INABA SATOSHI [JP]
- [XAY] US 2010287518 A1 20101111 - BECKER SCOTT T [US]
- [XI] US 2011317477 A1 20111229 - LIAW JHON JHY [TW]
- [X] US 2008001176 A1 20080103 - GOPALAKRISHNAN KAILASH [US], et al
- [X] WO 2006090445 A1 20060831 - FUJITSU LTD [JP], et al
- [X] US 2010301482 A1 20101202 - SCHULTZ RICHARD T [US], et al
- [X] KAWASAKI H ET AL: "Challenges and solutions of FinFET integration in an SRAM cell and a logic circuit for 22 nm node and beyond", ELECTRON DEVICES MEETING (IEDM), 2009 IEEE INTERNATIONAL, IEEE, PISCATAWAY, NJ, USA, 7 December 2009 (2009-12-07), pages 1 - 4, XP031644548, ISBN: 978-1-4244-5639-0
- See references of WO 2013106799A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)

WO 2013106799 A1 20130718; AU 2013207719 A1 20140731; AU 2013207719 B2 20160225; AU 2016202229 A1 20160505; AU 2016202229 B2 20180215; AU 2018200549 A1 20180215; AU 2018200549 B2 20191205; AU 2020201521 A1 20200319; CN 104303263 A 20150121; CN 104303263 B 20161214; CN 107424999 A 20171201; EP 2803077 A1 20141119; EP 2803077 A4 20151104; JP 2015506589 A 20150302; JP 2017224858 A 20171221; JP 2019054297 A 20190404; JP 6467476 B2 20190213; KR 101913457 B1 20181030; KR 20140114424 A 20140926; SG 10201605564W A 20160929; SG 11201404024Y A 20140828; TW 201349451 A 20131201; TW 201642440 A 20161201; TW 201717355 A 20170516; TW 201803084 A 20180116; TW I552307 B 20161001; TW I581403 B 20170501; TW I608593 B 20171211

DOCDB simple family (application)

US 2013021345 W 20130113; AU 2013207719 A 20130113; AU 2016202229 A 20160411; AU 2018200549 A 20180123; AU 2020201521 A 20200302; CN 201380013824 A 20130113; CN 201611023356 A 20130113; EP 13735704 A 20130113; JP 2014552360 A 20130113; JP 2017176032 A 20170913; JP 2019003098 A 20190111; KR 20147022592 A 20130113; SG 10201605564W A 20130113; SG 11201404024Y A 20130113; TW 102101384 A 20130114; TW 105125226 A 20130114; TW 106104453 A 20130114; TW 106134477 A 20130114